

INFORMATION DISCLOSURE
CITATION

ATTY. DOCKET NO.

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(To Be Assigned)

APPLICANT

CANHAM et al

FILING DATE

GROUP

(Use several sheets if necessary)

17 September 1997

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
MLT	5,348,618	9/20/94	CANHAM et al			

FOREIGN PATENT DOCUMENTS

DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
MLT	WO A 92 19084	10/29/92	WIPO		
MLT	0 618 624 A2	10/05/94	EUROPE		X

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

MLT	FIZIKA I TEKHNIKA POLUPROVODNIKOV, NOV. =DEC. 1993, RUSSIA, vol. 27, no. 11-12, ISSN 0015-3222, pages 1815-1819, XP000571557 BELYAKOV L V ET AL: "Efficient electroluminescence of porous silicon" cited in the application see the whole document.
	EUROPEAN MATERIALS RESEARCH SOCIETY 1993 SPRING MEETING 'LIGHT EMISSION FROM POROUS SILICON', vol. 57, no. 1-6, ISSN 0022-2313, JOURNAL OF LUMINESCENCE, NOV.-DEC. 1993, NETHERLANDS, pages 169-173, XP000573540 LANG W ET AL: "Porous silicon light-emitting p-n junction" cited in the application see the whole document.
	SEVENTH INTERNATIONAL CONFERENCE ON SOLID FILMS AND SURFACES, HSINCHU, TAIWAN, 12-16 DEC. 1994, vol. 92, ISSN 0169-4332, APPLIED SURFACE SCIENCE, FEB. 1996, ELSEVIER, NETHERLANDS, pages 598-605, XP000573563 MIMURA H ET AL: "Si-based optical devices using porous materials" see the whole document.
	39 TH AMERICAN VACUUM SOCIETY NATIONAL SYMPOSIUM, CHICAGO, IL, USA, 9-13 NOV. 1992, vol. 11, no. 4, pt.2, ISSN 0734-2101, JOURNAL OF VACUUM SCIENCE & TECHNOLOGY A(VACUUM, SURFACES, AND FILMS), JULY-AUG. 1993, USA, pages 1736-1738, XP000403687 KESAN V P ET AL: "Electroluminescence and photoluminescence from microporous silicon p-n junctions" cited in the application see the whole document.
	7 TH INTERNATIONAL CONFERENCE ON SOLID STATE SENSORS AND ACTUATORS (TRANSDUCERS '93), YOKOHAMA, JAPAN, 7-10 JUNE 1993, vol. A43, no. 1-3, ISSN 0924-4247, SENSORS AND ACTUATORS A (PHYSICAL), MAY 1994, SWITZERLAND, pages 153-156, XP000454102 KOZLOWSKI F ET AL: "Light-emitting diodes in porous silicon: cited in the application see the whole document.
MLT	ELECTRONICS LETTERS, 20 JULY 1995, UK, vol. 31, no. 15, ISSN 0013-5194, pages 1288-1289, XP000525797 LONI A ET AL: "Electroluminescent porous silicon device with an external quantum efficiency greater than 1.1% under CW operation" see page 1289, left-hand column, line 1-line 14.

*Examiner

Minhloan Tran

Date Considered

3/2003

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.

Form PTO-FB-A820 (Also PTO-1449)